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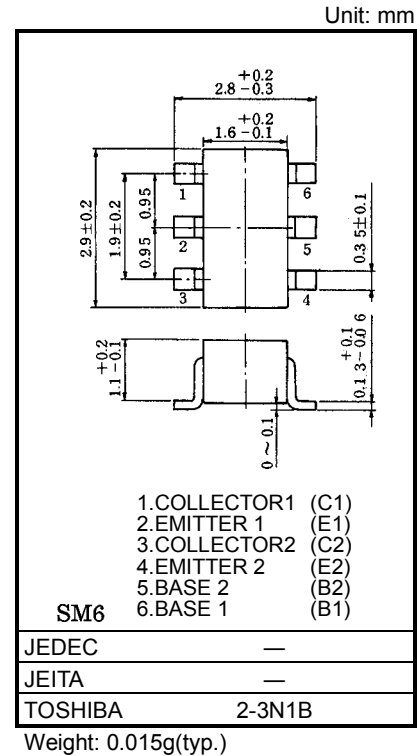
Audio Frequency General Purpose Amplifier Applications

- High voltage : $V_{CEO} = -120V$
- High h_{FE} : $h_{FE} = 200 \sim 700$
- Excellent h_{FE} linearity
: $h_{FE} (I_C = -0.1mA) / h_{FE} (I_C = -2mA) = 0.95$ (typ.)
- Low noise : $NF = 1dB$ (typ.)

Maximum Ratings ($T_a = 25^\circ C$) (Q1, Q2 Common)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-120	V
Collector-emitter voltage	V_{CEO}	-120	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-100	mA
Base current	I_B	-20	mA
Collector power dissipation	P_C^*	300	mW
Junction temperature	T_j	150	$^\circ C$
Storage temperature range	T_{stg}	-55~150	$^\circ C$

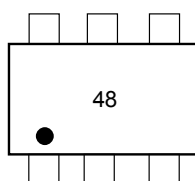
*Total rating. Power dissipation per element should not exceed 200mW.



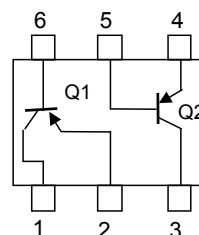
Electrical Characteristics ($T_a = 25^\circ C$) (Q1,Q2 Common)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	—	$V_{CB} = -120V, I_E = 0$	—	—	-0.1	μA
Emitter cut-off current	I_{EBO}	—	$V_{EB} = -5V, I_C = 0$	—	—	-0.1	μA
DC current gain	h_{FE}	—	$V_{CE} = -6V, I_C = -2mA$	200	—	700	
Collector-emitter saturation voltage	V_{CE}	—	$I_C = -10mA, I_B = -1mA$	—	—	-0.3	V
Transition frequency	f_T	—	$V_{CE} = -6V, I_C = -1mA$	—	100	—	MHz
Collector output capacitance	C_{ob}	—	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	4	—	pF
Noise figure	NF	—	$V_{CE} = -6V, I_C = -0.1mA$ $f = 1kHz, R_g = 10k\Omega$	—	1.0	—	dB

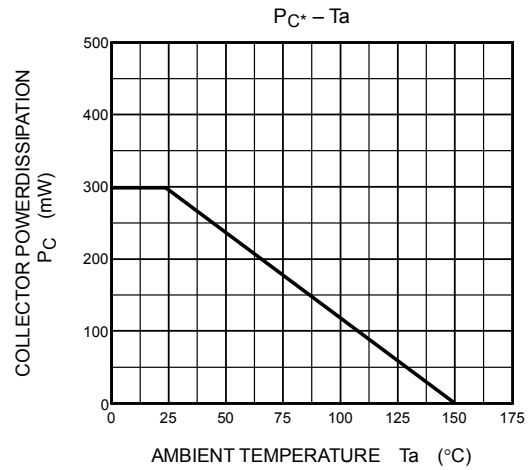
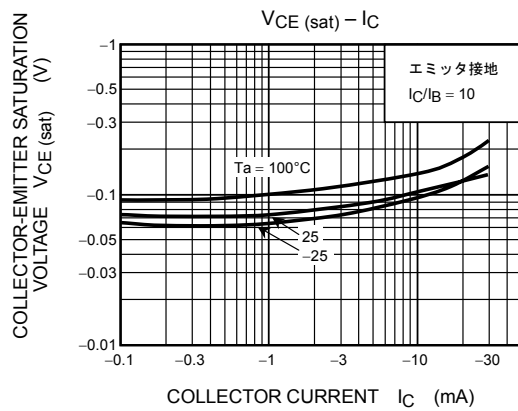
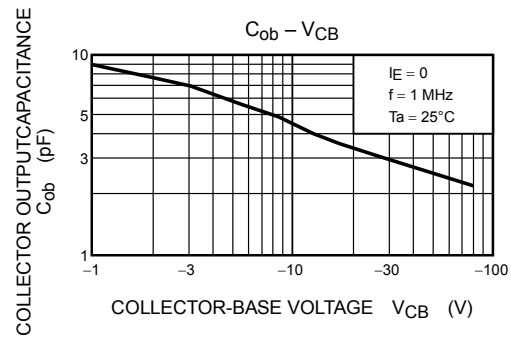
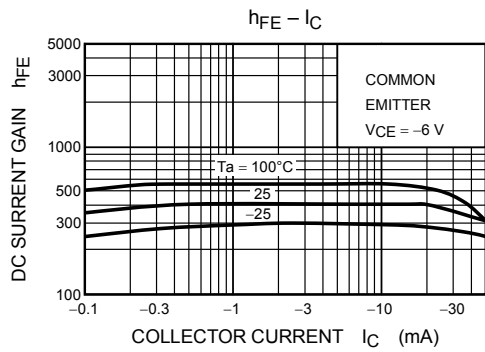
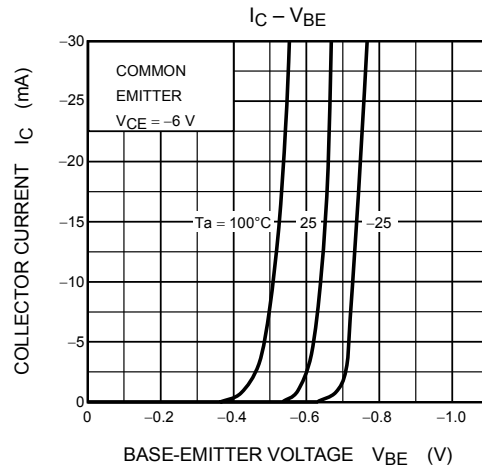
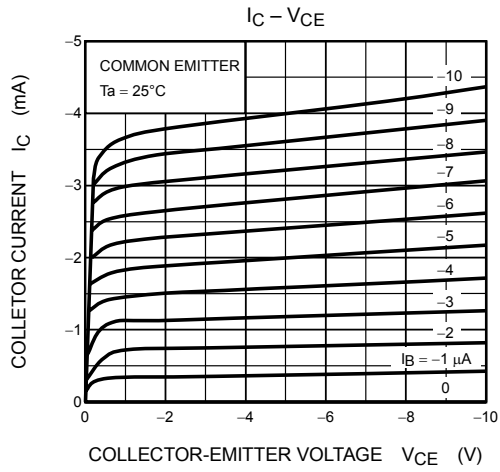
Marking



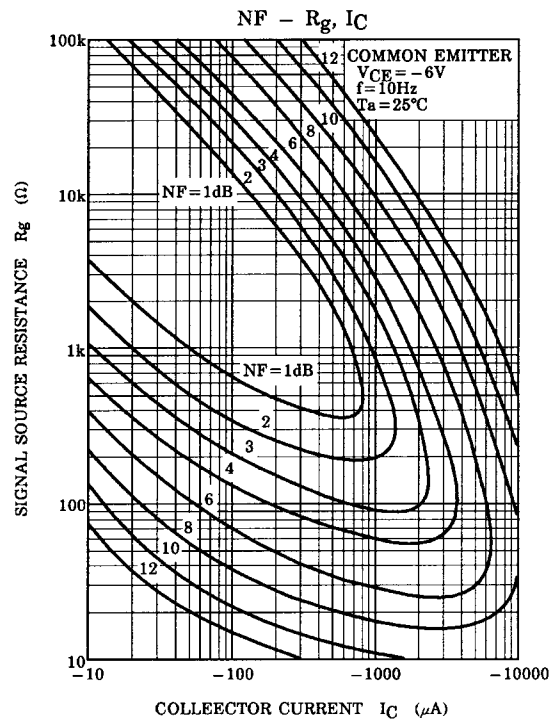
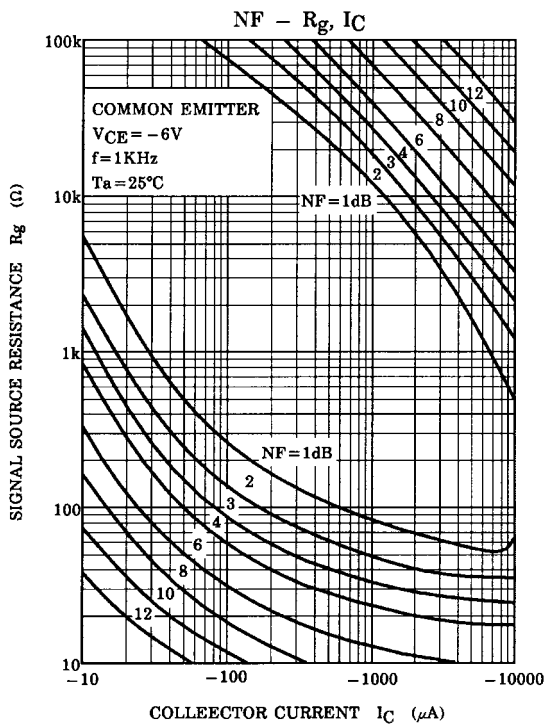
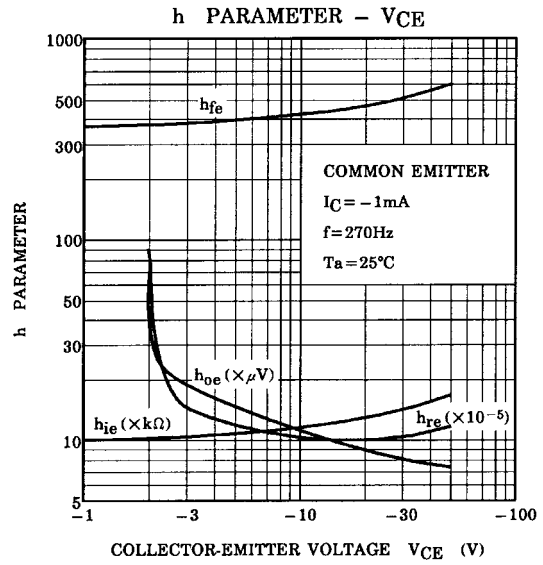
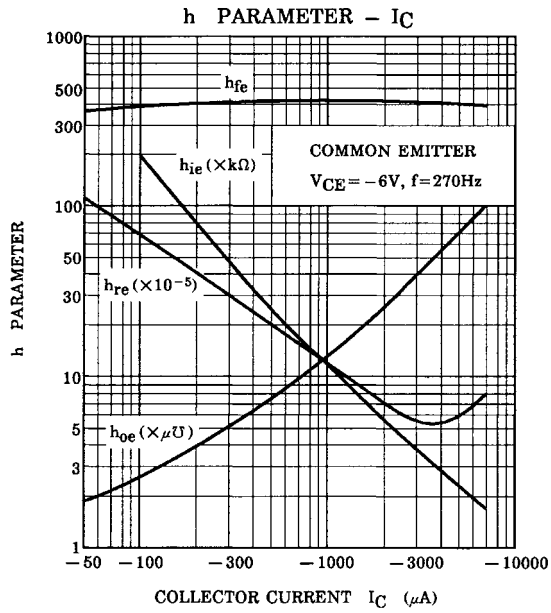
Equivalent Circuit (Top View)



(Q1,Q2 Common)



*Total Rating.



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